

10/526657
DT01 Rec'd PCT/PT 02 MAR 2005

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (original) SiCOI type composite substrate manufacturing method comprising the following steps :

- supply of an initial substrate comprising an Si or SiC support bearing a layer of SiO₂ whereon a thin layer of SiC is transferred,

- epitaxy of SiC on the thin layer of SiC,

wherein the epitaxy is conducted at the following temperatures :

- from 1450°C to obtain 6H or 4H polytype epitaxy on a transferred thin 6H or 4H polytype layer respectively, if the support consists of SiC,

- from 1350°C to obtain 3C polytype epitaxy on a transferred thin 3C polytype layer, if the support consists of Si or SiC,

- from 1350°C to obtain 6H or 4H polytype epitaxy on a transferred thin 6H or 4H polytype layer respectively, if the support consists of Si.

2. (original) Method according to claim 1, wherein before the epitaxy step, an initial substrate preparation step is provided for to improve the surface quality of the transferred thin SiC layer.

3. (original) Method according to claim 2, wherein the preparation step consists of subjecting the surface of the transferred thin SiC layer to an operation selected from polishing, etching and hydrogen etching.

4. (original) Method according to claim 1, wherein several SiC layers are successively grown epitaxially on the thin SiC layer.
5. (currently amended) Use of the SiCOI type composite substrate obtained by means of the manufacturing method according to claim 1 ~~any of claims 1 to 4~~ to produce semiconductor devices.
6. (currently amended) Semiconductor device produced on an SiCOI type composite substrate obtained by means of the manufacturing method according to claim 1 ~~any of claims 1 to 4~~.